

RoHS

COMPLIANT

HALOGEN

FREE

ailable

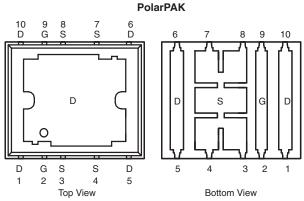
Vishay Siliconix

## N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY								
		I <sub>D</sub> (A) <sup>a</sup>						
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) <sup>e</sup>	Silicon Limit	Package Limit	Q <sub>g</sub> (Typ.)				
20	0.0016 at V <sub>GS</sub> = 10 V	220	60	46 nC				
20	0.0025 at V <sub>GS</sub> = 4.5 V	117	60	40110				

Package Drawing

www.vishay.com/doc?72945

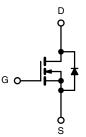


#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Gen II Power MOSFET
- Ultra Low Thermal Resistance Using Top-Exposed PolarPAK<sup>®</sup> Package for Double-Sided Cooling
- Leadframe-Based New Encapsulated Package
  - Die Not Exposed
- Same Layout Regardless of Die Size
- Low  $Q_{gd}/Q_{gs}$  Ratio Helps Prevent Shoot-Through 100 %  $R_g$  and UIS Tested
- Compliant to RoHS directive 2002/95/EC

#### **APPLICATIONS**

- VRM
- DC/DC Conversion: Low-Side
- Synchronous Rectification



N-Channel MOSEET For Related Documents www.vishay.com/ppg?73739

Top surface is connected to pins 1, 5, 6, and 10

Ordering Information: SiE808DF-T1-E3 (Lead (Pb)-free) SiE808DF-T1-GE3 (Lead (Pb)-free and Halogen-free)

#### ABSOLUTE MAXIMUM RATINGS T<sub>A</sub> = 25 °C, unless otherwise noted Symbol Limit Unit Parameter Drain-Source Voltage V<sub>DS</sub> 20 ٧ V<sub>GS</sub> Gate-Source Voltage ± 20 220 (Silicon Limit) T<sub>C</sub> = 25 °C 60<sup>a</sup> (Package Limit) Continuous Drain Current (T<sub>J</sub> = 150 °C) T<sub>C</sub> = 70 °C $I_D$ 60<sup>a</sup> 45<sup>b, c</sup> T<sub>A</sub> = 25 °C 36<sup>b, c</sup> T<sub>A</sub> = 70 °C А Pulsed Drain Current 100 $I_{DM}$ T<sub>C</sub> = 25 °C 60<sup>a</sup> Continuous Source-Drain Diode Current ls T<sub>A</sub> = 25 °C 4.3<sup>b, c</sup> Single Pulse Avalanche Current I<sub>AS</sub> 35 L = 0.1 mHAvalanche Energy EAS 61 mJ T<sub>C</sub> = 25 °C 125 T<sub>C</sub> = 70 °C 80 Maximum Power Dissipation $\mathsf{P}_\mathsf{D}$ w 5.2<sup>b, c</sup> T<sub>A</sub> = 25 °C T<sub>A</sub> = 70 °C 3.3<sup>b, c</sup> Operating Junction and Storage Temperature Range T<sub>J</sub>, T<sub>stg</sub> - 55 to 150 °C Soldering Recommendations (Peak Temperature)<sup>d, e</sup> 260

Notes:

a. Package limited is 60 A.

Surface Mounted on 1" x 1" FR4 board. b.

c. t = 10 s.

See Solder Profile (www.vishay.com/doc?73257). The PolarPAK is a leadless package. The end of the lead terminal is exposed copper (not d. plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not requiréd to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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### **THERMAL RESISTANCE RATINGS**

Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a, b</sup>	t ≤ 10 s	R <sub>thJA</sub>	20	24	
Maximum Junction-to-Case (Drain Top)	Steady State	R <sub>thJC</sub> (Drain)	0.8	1	°C/W
Maximum Junction-to-Case (Source) <sup>a, c</sup>	Sleady Slale	R <sub>thJC</sub> (Source)	2.2	2.7	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Maximum under Steady State conditions is 68 °C/W.

c. Measured at source pin (on the side of the package).

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	<u> </u>					
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	20			V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$			26.5		24/20
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = 250 μA		- 7.3		mV/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	1.5	2.3	3	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zana Oata Maltana Duain Ourrent	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1	μA
Zero Gate Voltage Drain Current		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 V, V_{GS} = 10 V$	25			Α
	P	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 25 A		0.0013	0.0016	Ω
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 25 \text{ A}$		0.0021	0.0025	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 25 A		95		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			8800		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1600		
Reverse Transfer Capacitance	C <sub>rss</sub>			600		
Tatal Cata Charge	Q <sub>g</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 25 \text{ A}$		102	155	
Total Gate Charge				46	70	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 4.5 V, $I_{D}$ = 20 A		26		nC
Gate-Drain Charge	Q <sub>gd</sub>			8		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		0.9	1.35	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			180	270	
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 1 $\Omega$		215	325	
Turn-Off Delay Time	t <sub>d(off)</sub>	${ m I}_{ m D}\cong$ 10 A, ${ m V}_{ m GEN}$ = 4.5 V, ${ m R}_{ m g}$ = 1 $\Omega$		50	75	
Fall Time	t <sub>f</sub>			15	25	20
Turn-On Delay Time	t <sub>d(on)</sub>			25	40	ns
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 1 $\Omega$		55	85	
Turn-Off Delay Time	t <sub>d(off)</sub>	${ m I}_{ m D}\cong$ 10 A, ${ m V}_{ m GEN}$ = 10 V, ${ m R}_{ m g}$ = 1 $\Omega$		55	85	
Fall Time	t <sub>f</sub>			10	15	
Drain-Source Body Diode Characteristi	cs					
Continuous Source-Drain Diode Current	ا <sub>S</sub>	T <sub>C</sub> = 25 °C			60	А
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				100	~
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 10 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>			56	85	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 10 A, dl/dt = 100 A/μs, T <sub>.1</sub> = 25 °C		60	90	nC
Reverse Recovery Fall Time	t <sub>a</sub>	$F = 10 \text{ A}, \text{ u/u} = 100 \text{ A/}\mu\text{s}, 1\text{ J} = 25 \text{ C}$		26		
Reverse Recovery Rise Time	t <sub>b</sub>			30		ns

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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## SiE808DF

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 $T_C =$ 

3.5

3.0

 $C_{\text{iss}}$ 

10

50

75

100

 $V_{GS} = 4.5 \text{ V}, 10 \text{ V}$ I<sub>D</sub> = 25 A

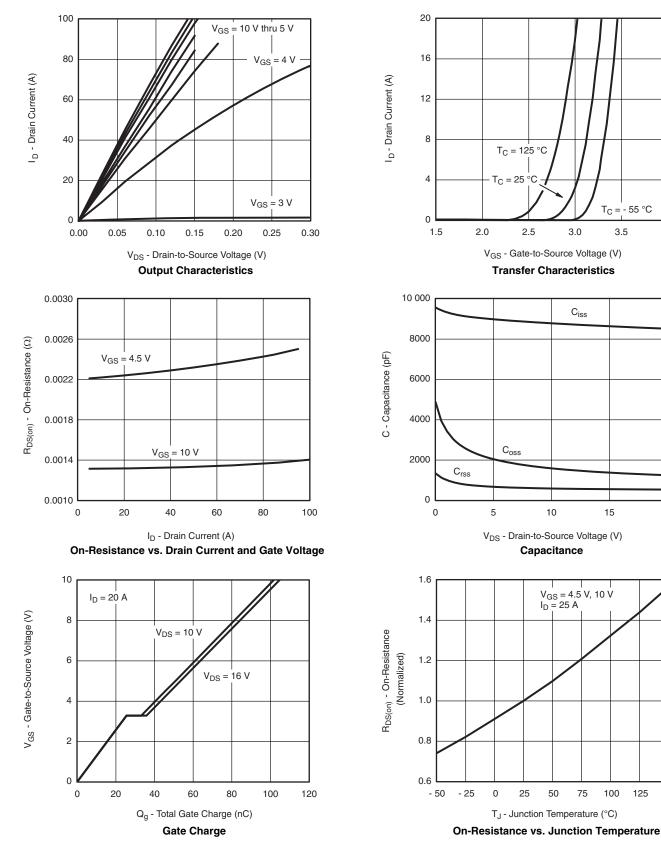
15

- 55 °C

4.0

20

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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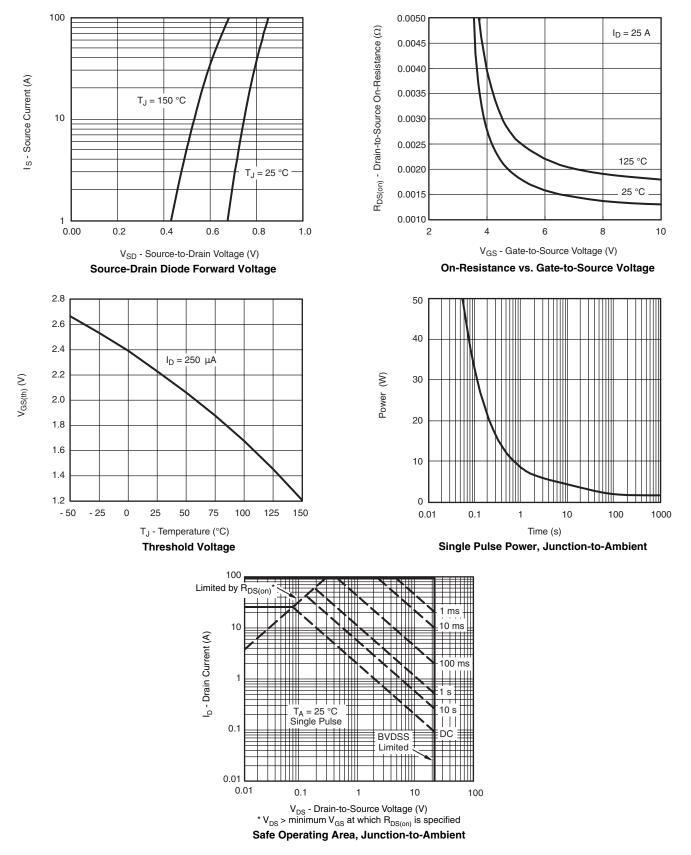
150

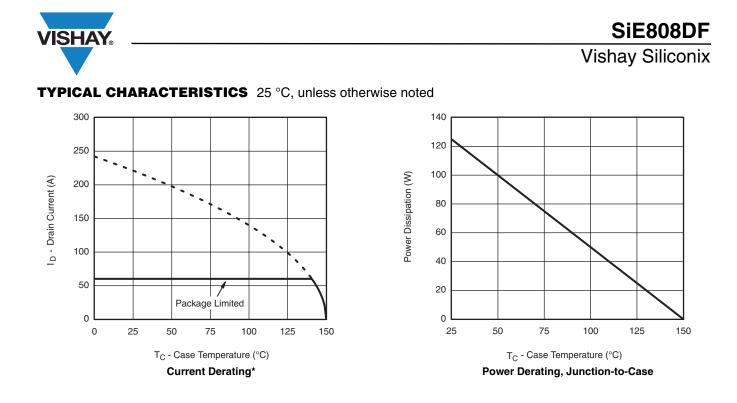
## SiE808DF



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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



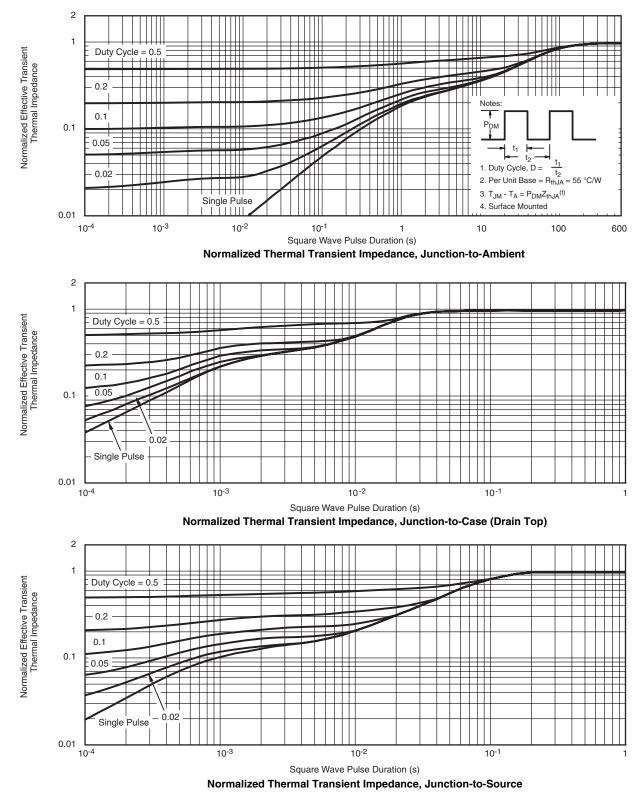


\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?73739">www.vishay.com/ppg?73739</a>.

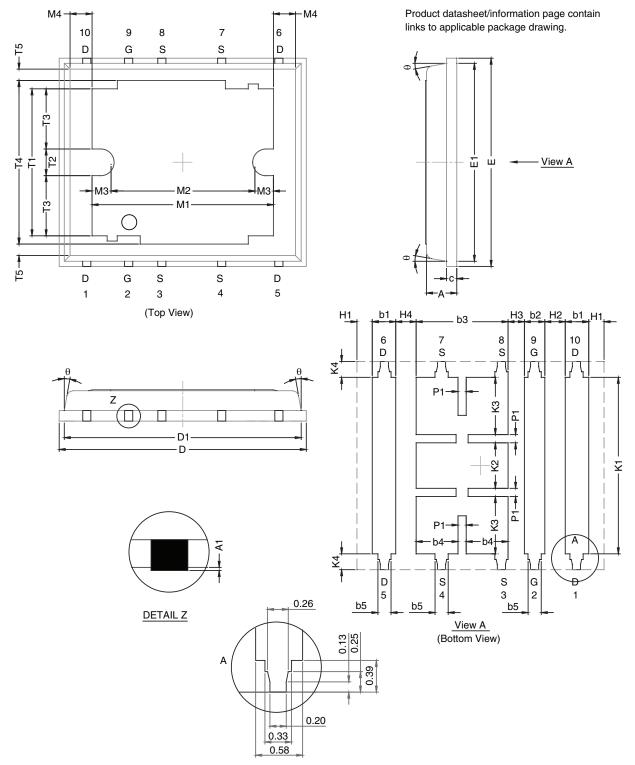
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# Package Information

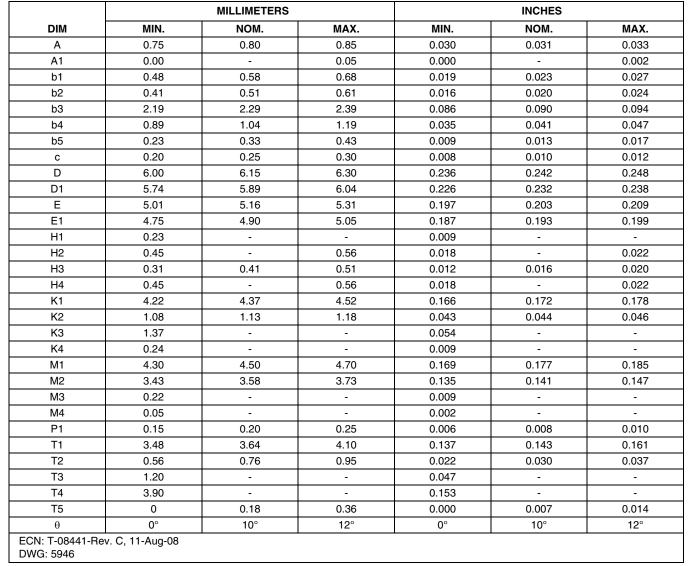
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#### **POLARPAK™ OPTION L**



## **Package Information**

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#### Notes

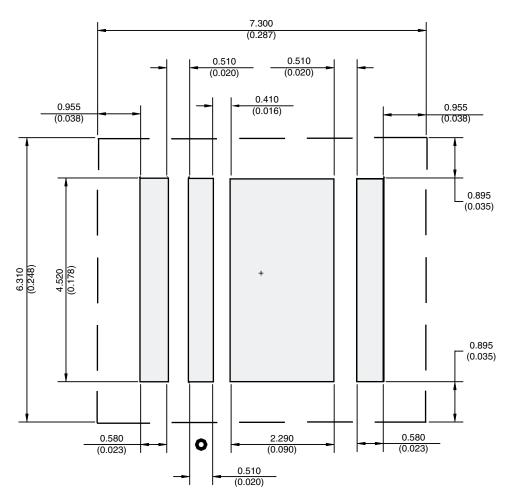
Millimeters govern over inches.



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### RECOMMENDED MINIMUM PADS FOR PolarPAK® Option L and S



Recommended Minimum for PolarPAK Option L and S Dimensions in mm/(Inches) No External Traces within Broken Lines Dot indicates Gate Pin (Part Marking)

APPLICATION NOTE

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